

Substitute for form 1449A-PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet 1 of 1

Complete if known

Applicant Number	10/043065
Filing Date	January 9, 2002
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Meier, Stephen

Attorney Docket No: 303.684US3

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
JP	US-5,852,311	12/22/1998	Kwon, et al.			06/05/1997
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/043065
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	First Named Inventor	Forbes, Leonard
	Group Art Unit	2822
	Examiner Name	Rose, Kiesha
Sheet 1 of 1	Attorney Docket No: 303.684US3	



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	US-6,605,961	08/12/2003	Forbes, L.	326	41	02/29/2000
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	US-2003/0201491	10/30/2003	Chung, B.	257	324	05/08/2003
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KR		CHAU, R. , et al., "30nm Physical Gate Length CMOS Tansistors with 1.0 ps n-MOS and 1.7 ps p-MOS Gate Delays", <u>IEEE Int. Electron. Devices Meeting, San Francisco, (December, 2000),pp. 45-48</u>	
I		FRANK, J. , et al., "Monte Carlo Simulations of p- and n-Channel Dual-Gate Si MOSFET's at the Limits of Scaling", <u>IEEE Transactions on Electron Devices, 40(11), (November 1993),pg. 2103</u>	
I		HIRAYAMA, M. , et al., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", <u>IEEE, (1999),4 pages</u>	
KR		ILYAS, M. , et al., "The optical absorption edge of amorphous thin films of silicon monoxide and of silicon monoxide mixed with titanium monoxide", <u>IEE, (2001),1</u>	

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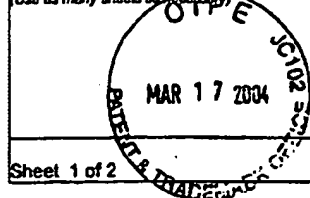
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KR		page MULLER, D. A., "The Electronic Structure at the Atomic Scale of Ultrathin Gate Oxides", <u>Nature</u> , 399, (June 1999),758-761	
I		OHGURO, T. , "Tenth Micron P-MOSFET's with Ultra-Thin Epitaxial Channel Layer Grown by Ultra-High-Vacuum CVD", <u>Proceedings: International Electron Devices Meeting, IEEE, Washington, Dec. 5-8, 1993,(Dec. 5, 1993),pp. 433-436</u>	
I		STRASS, A. , et al., "Fabrication and Characterisation of thin low-temperature MBE-compatible silicon oxides of different stoichiometry", <u>Thin Solid Films</u> 349, (1999),pp. 135-146	
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 Group Art Unit 2822
 Examiner Name Rose, Kiesha

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		FRANK, J. , et al., "Monte Carlo Simulations of p- and n-Channel Dual-Gate Si MOSFET's at the Limits of Scaling", <u>IEEE Transactions on Electron Devices, 40(11), (November 1993), pp. 2103</u>	
		HIRAYAMA, M. , et al., "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", <u>IEEE, (1999), 4 pages</u>	
		ILYAS, M. , et al., "The optical absorption edge of amorphous thin films of silicon monoxide and of silicon monoxide mixed with titanium monoxide", <u>IEE, (2001), 1</u>	

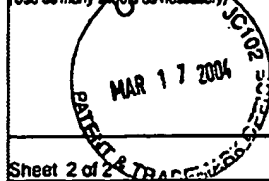
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		STRASS, A., et al., "Fabrication and Characterisation of thin low-temperature MBE-compatible silicon oxides of different stoichiometry", <u>Thin Solid Films</u> 349, (1999), pp. 135-146	
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